S93VP462/S93VP463

VOLTAGE-SENSE™ Write Protected Memory

FEATURES

- **Voltage-Sense Write Protection**
  - **— Low V_{CC} Write Lockout**
  - **— All Writes Inhibited when $V_{CC} < V_{TRIP}$**
  - **— Protects Against Inadvertent Writes During**
    - **Power-up**
    - **Power-down**
    - **Brown-out Conditions**
  - **— All Devices 'Readable' from 1.8V to 5.5V**
    - **User Selectable V_{TRIP} Levels**
- **Memory**
  - **— 1K-bit Microwire Memory**
  - **— S93VP462**
    - **– Internally Ties ORG Low**
    - **– 100% Compatible with All 8-bit Implementations**
    - **– Sixteen Byte Page Write Capability**
  - **— S93VP463**
    - **– Internally Ties ORG High**
    - **– 100% Compatible With all 16-bit Implementations**
    - **– Eight Word Page Write Capability**

APPLICATIONS

New designs for applications where data corruption cannot be permitted.

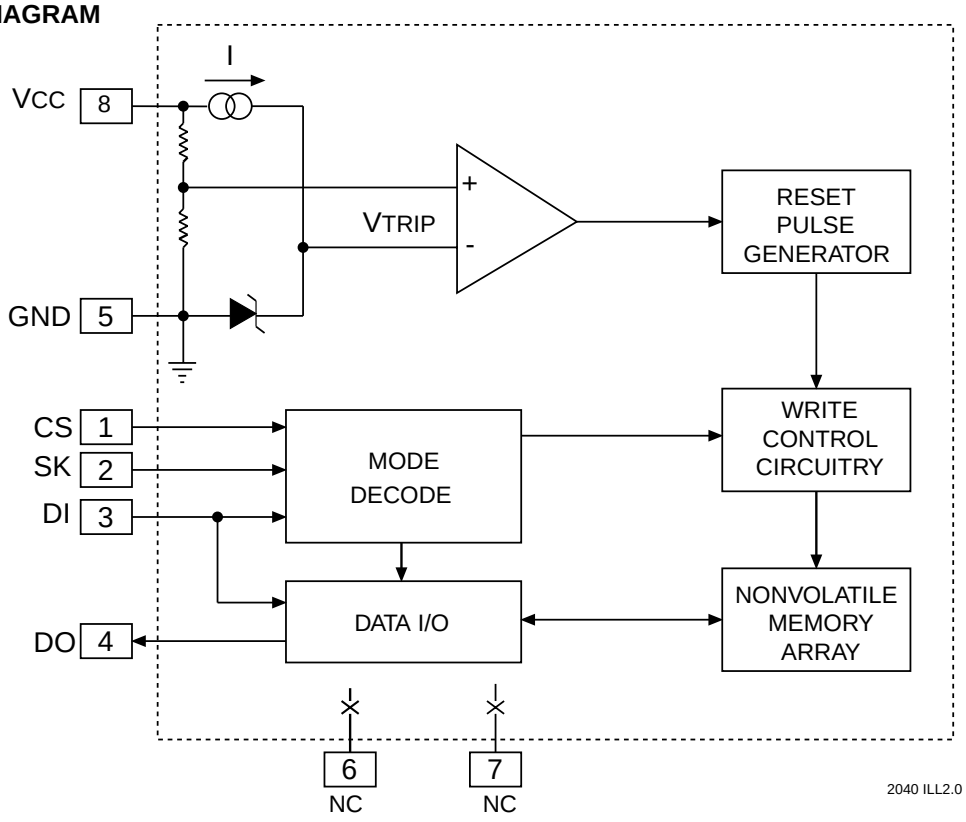
Replacement of existing industry standard 1K memories.

OVERVIEW

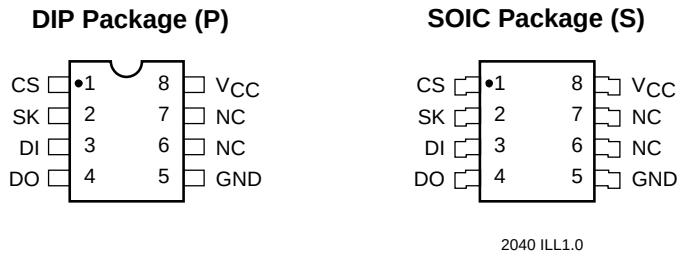
The S93VP462 and S93VP463 are voltage monitoring memory devices that write protect the array from inadvertent writes whenever V_{CC} is below V_{TRIP}.

Both devices have 1k-bits of E^2PROM memory that is accessible via the industry standard microwire bus. The S93VP462 is configured with an internal ORG pin tied low providing a 8-bit byte organization and the S93VP463 is configured with an internal ORG pin tied high providing a 16-bit word organization. Both the S93VP462 and S93VP463 have page write capability. The devices are designed for a minimum 1,000,000 program/erase cycles and have data retention in excess of 100 years.

BLOCK DIAGRAM



PIN CONFIGURATION



PIN FUNCTIONS

Pin Name	Function
CS	Chip Select
SK	Clock Input
DI	Serial Data Input
DO	Serial Data Output
V_{CC}	+2.7 to 6.0V Power Supply
GND	Ground
NC	No Connect

DEVICE OPERATION

WRITE LOCKOUT DESCRIPTION

The S93VP462/VP463 provides a precision internal reset controller that ensures correct system operation during brown-out and power-up/-down conditions.

During power-up, the write lockout remains active until V_{CC} reaches the V_{TRIP} threshold. Write lockout will continue to be driven for approximately 150 ms after V_{CC} reaches V_{TRIP}. During power-down, write lockout will be driven active when even V_{CC} falls below V_{TRIP}.

GENERAL OPERATION

The S93VP462/VP463 is a 1024-bit nonvolatile memory intended for use with industry standard microprocessors. The S93VP463 is organized as X16, seven 9-bit instructions control the reading, writing and erase operations of the device. The S93VP462 is organized as X8, seven 10-bit instructions control the reading, writing and erase operations of the device. The device operates on a single 3V or 5V supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data from the device, or when checking the ready/busy status after a write operation.

The ready/busy status can be determined after the start of a write operation by selecting the device (CS high) and polling the DO pin; DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. See the Applications Aid section for detailed use of the ready busy status.

The format for all instructions is: one start bit; two op code bits and either six (x16) or seven (x8) address or instruction bits.

Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the S93VP462/VP463 will come out of the high impedance state and, will first output an initial dummy zero bit, then begin shifting out the data addressed (MSB first). The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay (t_{PD0} or t_{PD1}).

Write

After receiving a WRITE command, address and the data, the CS (Chip Select) pin must be deselected for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start automatic erase and write cycle to the memory location specified in the instruction. The ready/busy status of the S93VP462/VP463 can be determined by selecting the device and polling the DO pin.

Erase

Upon receiving an ERASE command and address, the CS (Chip Select) pin must be deselected for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start the auto erase cycle of the selected memory location. The ready/busy status of the S93VP462/VP463 can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical “1” state.

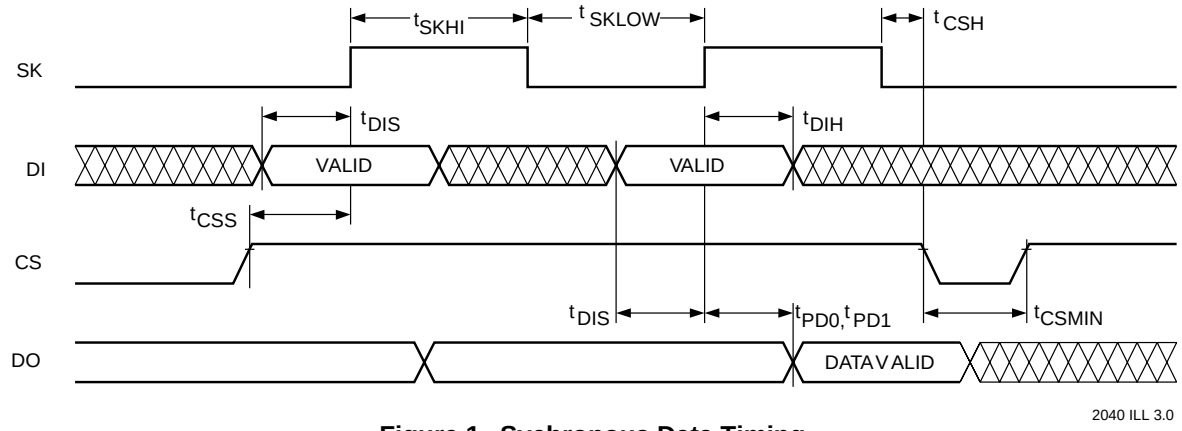


Figure 1. Sychronous Data Timing

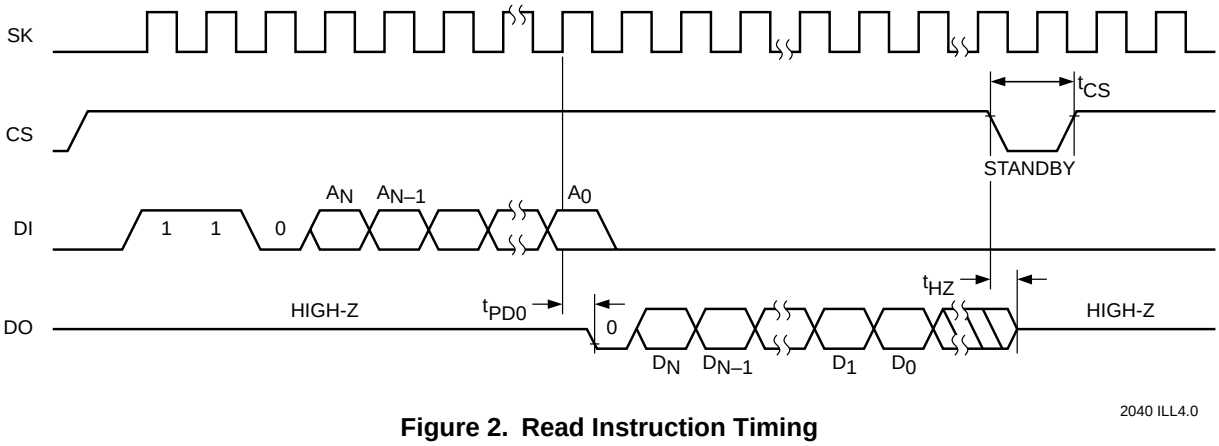


Figure 2. Read Instruction Timing

Erase/Write Enable and Disable
The S93VP462/VP463 powers up in the write disable state. Any writing after power-up or after an EWDS (write disable) instruction must first be preceded by the EWEN (write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all S93VP462/VP463 write and clear instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/disable status.

Erase All
Upon receiving an ERAL command, the CS (Chip Select) pin must be deselected for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the S93VP462/VP463 can be determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits will be in a logical "1" state.

Write All
Upon receiving a WRAL command and data, the CS (Chip Select) pin must be deselected for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the S93VP462/VP463 can be determined by selecting the device and polling the DO pin. It is not necessary for all memory locations to be cleared before the WRAL command is executed.

Page Write
93462 - Assume WEN has been issued. The host will then take CS high, and begin clocking in the start bit, write command and 7-bit address immediately followed by the first byte of data to be written. The host can then continue clocking in 8-bit bytes of data with each byte to be written to the next higher address. Internally the address pointer is incremented after receiving each group of eight clocks; however, once the address counter reaches xxx 1111 it will roll over to xxx 0000 with the next clock. After the last bit is clocked in no internal write operation will occur until CS is brought low.

93463 - Assume WEN has been issued. The host will then take CS high, and begin clocking in the start bit, write command and 6-bit address immediately followed by the first 16-bit word of data to be written. The host can then continue clocking in 16-bit words of data with each word to be written to the next higher address. Internally the address pointer is incremented after receiving each group of sixteen clocks; however, once the address counter reaches xxx x111 it will roll over to xx x000 with the next clock. After the last bit is clocked in no internal write operation will occur until CS is brought low.

Continuous Read
This begins just like a standard read with the host issuing a read instruction and clocking out the data byte [word]. If the host then keeps CS high and continues generating clocks on SK, the S93VP462/VP463 will output data from the next higher address location. The S93VP462/VP463 will continue incrementing the address and outputting data so long as CS stays high. If the highest address is reached, the address counter will roll over to address 0000. CS going low will reset the instruction register and any subsequent read must be initiated in the normal manner of issuing the command and address.

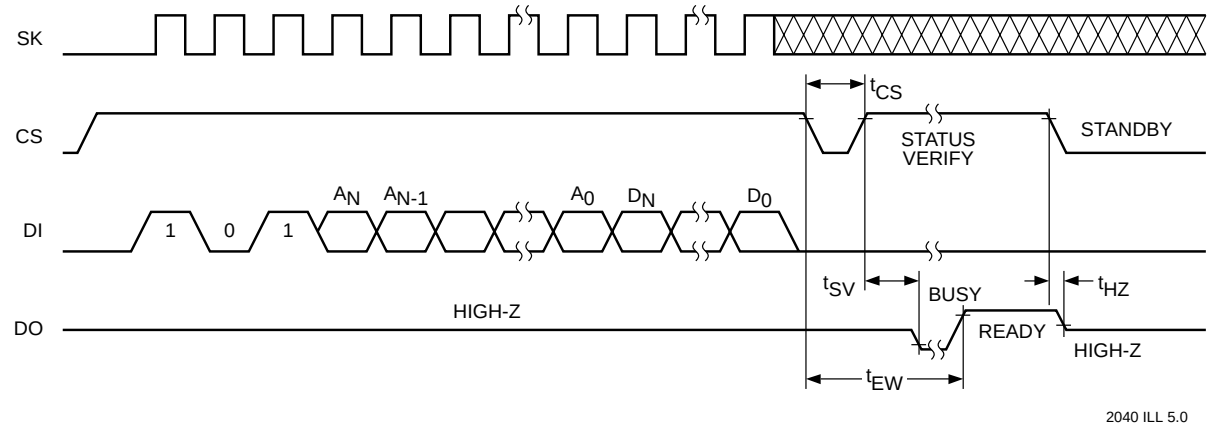


Figure 3. Write Instruction Timing

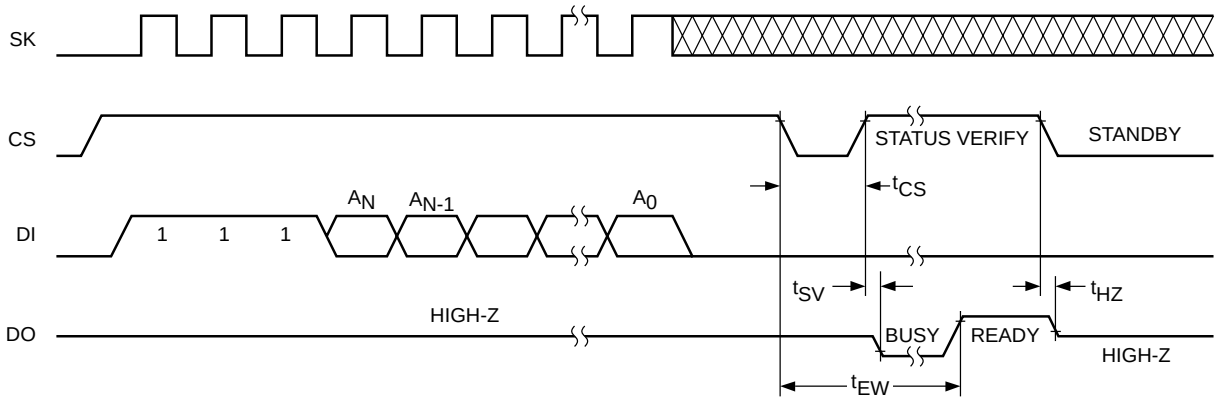


Figure 4. Erase Instruction Timing

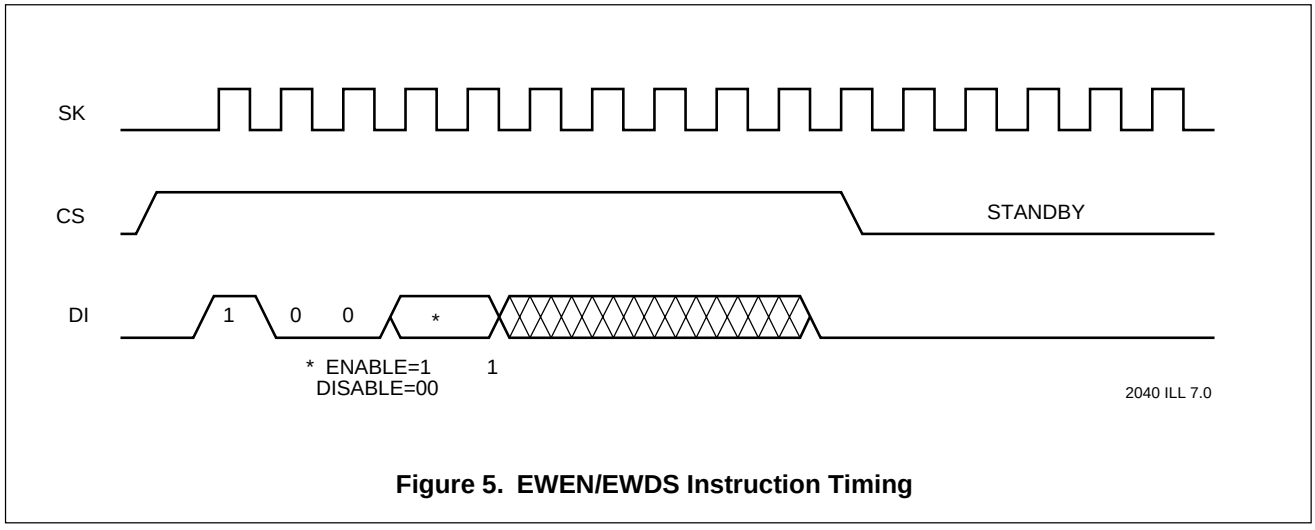


Figure 5. EWEN/EWDS Instruction Timing

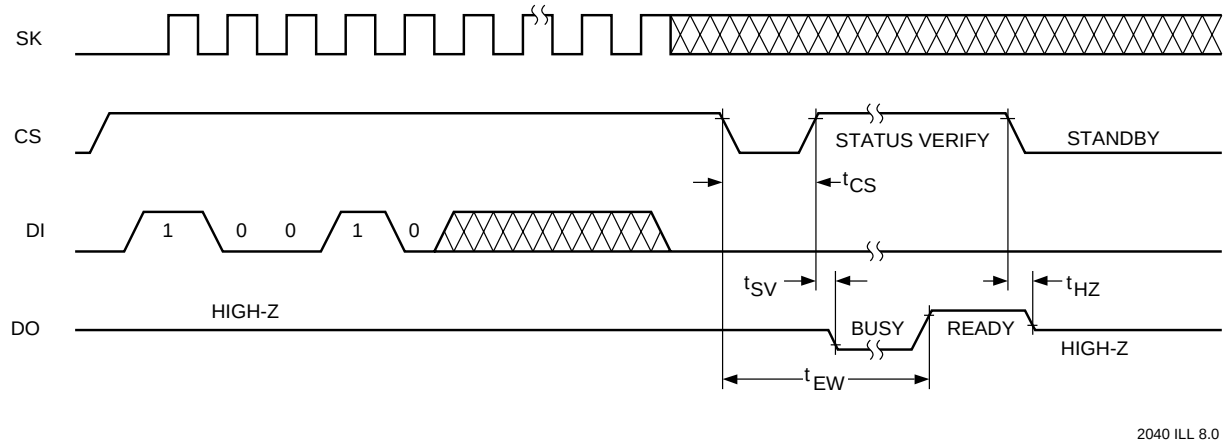


Figure 6. ERAL Instruction Timing

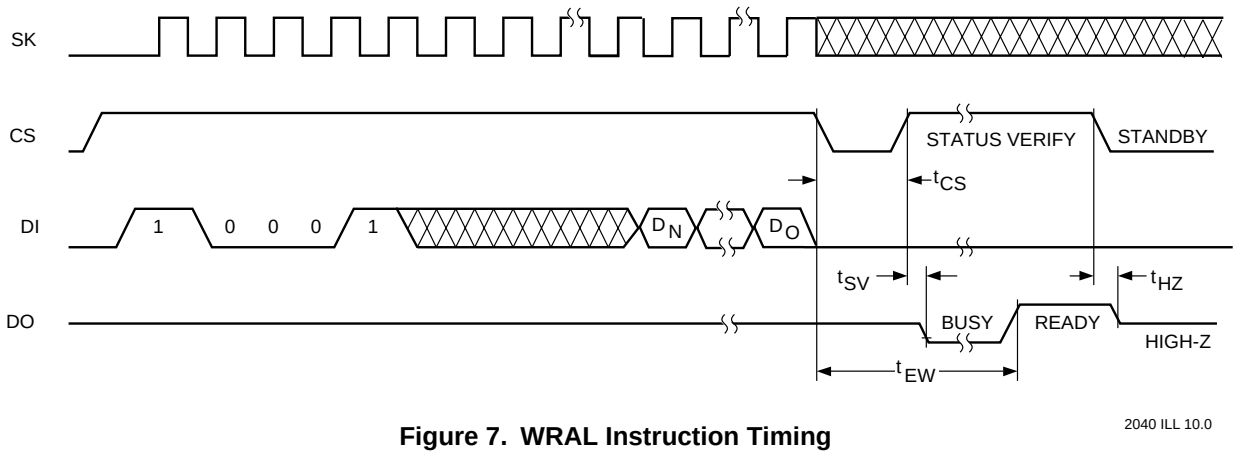


Figure 7. WRAL Instruction Timing

INSTRUCTION SET

Instruction	Start Bit	Opcode	Address		Data		Comments
			x8	x16	x8	x16	
READ	1	10	A6–A0	x(A5–A0)			Read Address AN–A0
ERASE	1	11	A6–A0	x(A5–A0)			Clear Address AN–A0
WRITE	1	01	A6–A0	x(A5–A0)	D7–D0	D15–D0	Write Address AN–A0
EWEN	1	00	11xxxxx	11xxxx			Write Enable
EWDS	1	00	00xxxxx	00xxxx			Write Disable
ERAL	1	00	10xxxxx	10xxxx			Clear All Addresses
WRAL	1	00	01xxxxx	01xxxx	D7–D0	D15–D0	Write All Addresses

2040 PGM T5.0

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias ..... –55°C to +125°C
Storage Temperature ..... –65°C to +150°C
Voltage on any Pin with Respect to Ground(1) ..... –2.0V to +V_{CC} +2.0V
V_{CC} with Respect to Ground ..... –2.0V to +7.0V
Package Power Dissipation Capability (Ta = 25°C) 1.0W
Lead Soldering Temperature (10 secs) ..... 300°C
Output Short Circuit Current(2) ..... 100 mA

***COMMENT**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RECOMMENDED OPERATING CONDITIONS

Temperature	Min	Max
Commercial	0°C	+70°C
Industrial	-40°C	+85°C

2040 PGM T7.0

RELIABILITY CHARACTERISTICS

Symbol	Parameter	Min.	Max.	Units	Reference Test Method
N_{END}(3)	Endurance	1,000,000		Cycles/Byte	MIL-STD-883, Test Method 1033
T_{DR}(3)	Data Retention	100		Years	MIL-STD-883, Test Method 1008
V_{ZAP}(3)	ESD Susceptibility	2000		Volts	MIL-STD-883, Test Method 3015
I_{LTH}(3)(4)	Latch-Up	100		mA	JEDEC Standard 17

2040 PGM T2.0

D.C. OPERATING CHARACTERISTICS (over recommended operating conditions unless otherwise specified)

		Limits				
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_{CC}	Power Supply Current (Operating)			3	mA	DI = 0.0V, f_{SK} = 1MHz V_{CC} = 5.0V, CS = 5.0V, Output Open
I_{SB}	Power Supply Current (Standby)			50	µA	CS = 0V Reset Outputs Open
I_{LI}	Input Leakage Current			2	µA	V_{IN} = 0V to V_{CC}
I_{LO}	Output Leakage Current (Including ORG pin)			10	µA	V_{OUT} = 0V to V_{CC}, CS = 0V
V_{IL1} V_{IH1}	Input Low Voltage Input High Voltage	-0.1 2		0.8 V_{CC}+1	V V	4.5V≤V_{CC}<5.5V
V_{IL2} V_{IH2}	Input Low Voltage Input High Voltage	0 V_{CC}X0.7		V_{CC}X0.2 V_{CC}+1	V V	1.8V≤V_{CC}<2.7V
V_{OL1} V_{OH1}	Output Low Voltage Output High Voltage	2.4		0.4	V V	4.5V≤V_{CC}<5.5V I_{OL} = 2.1mA I_{OH} = -400µA
V_{OL2} V_{OH2}	Output Low Voltage Output High Voltage	V_{CC}-0.2		0.2	V V	1.8V≤V_{CC}<2.7V I_{OL} = 1mA I_{OH} = -100µA

2040 PGM T3.0

Note:
(1) The minimum DC input voltage is –0.5V. During transitions, inputs may undershoot to –2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5V, which may overshoot to V_{CC} +2.0V for periods of less than 20 ns.
(2) Output shorted for no more than one second. No more than one output shorted at a time.
(3) This parameter is tested initially and after a design or process change that affects the parameter.
(4) Latch-up protection is provided for stresses up to 100 mA on address and data pins from –1V to V_{CC} +1V.

PIN CAPACITANCE

Symbol	Test	Max.	Units	Conditions
C_{OUT}(1)	OUTPUT CAPACITANCE (DO)	5	pF	V_{OUT}=OV
C_{IN}(1)	INPUT CAPACITANCE (CS, SK, DI, ORG)	5	pF	V_{IN}=OV

Note: 2040 PGM T4.0

(1) This parameter is tested initially and after a design or process change that affects the parameter.

A.C. CHARACTERISTICS (over recommended operating conditions unless otherwise specified)

		Limits					
		V_{CC}=2.7V-4.5V		V_{CC}=4.5V-5.5V			Test
SYMBOL	PARAMETER	Min.	Max.	Min.	Max.	UNITS	Conditions
t_{CSS}	CS Setup Time	100		50		ns	C_L = 100pF
t_{CSH}	CS Hold Time	0		0		ns	
t_{DIS}	DI Setup Time	200		100		ns	
t_{DIH}	DI Hold Time	200		100		ns	
t_{PD1}	Output Delay to 1		0.5		0.25	µs	
t_{PD0}	Output Delay to 0		0.5		0.25	µs	
t_{HZ}(1)	Output Delay to High-Z		200		100	ns	
t_{EW}	Program/Erase Pulse Width		10		10	ms	
t_{CSMIN}	Minimum CS Low Time	0.5		0.25		µs	
t_{SKHI}	Minimum SK High Time	0.5		0.25		µs	
t_{SKLOW}	Minimum SK Low Time	0.5		0.25		µs	
t_{SV}	Output Delay to Status Valid		0.5		0.25	µs	
SK_{MAX}	Maximum Clock Frequency	DC	500	DC	1000	KHZ	

Note: 2040 PGM T6.0

(1) This parameter is tested initially and after a design or process change that affects the parameter.

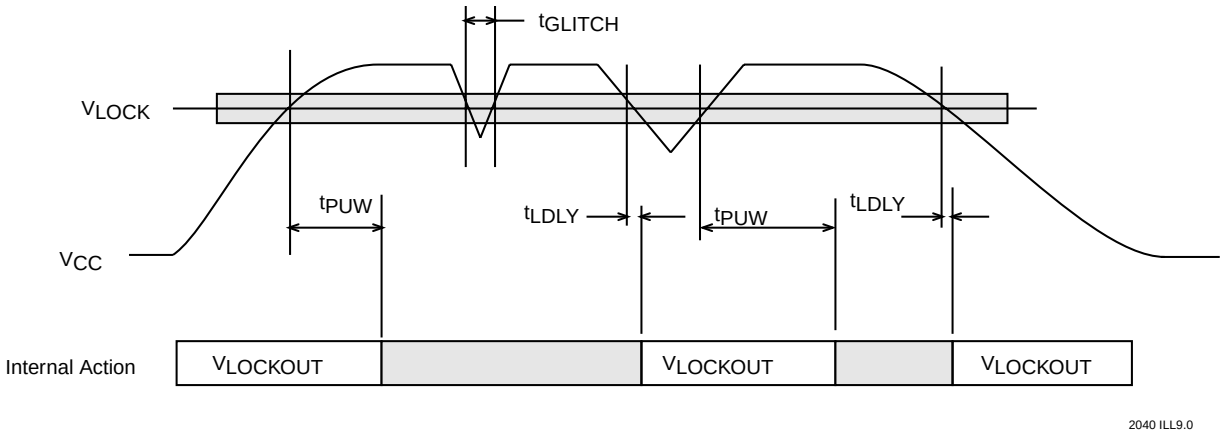
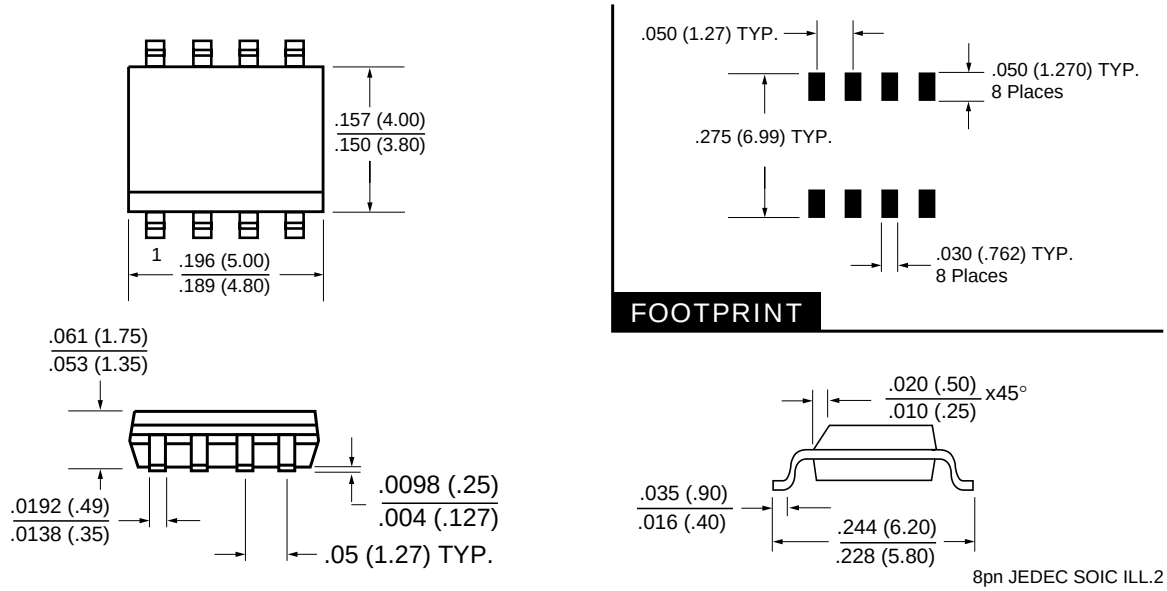


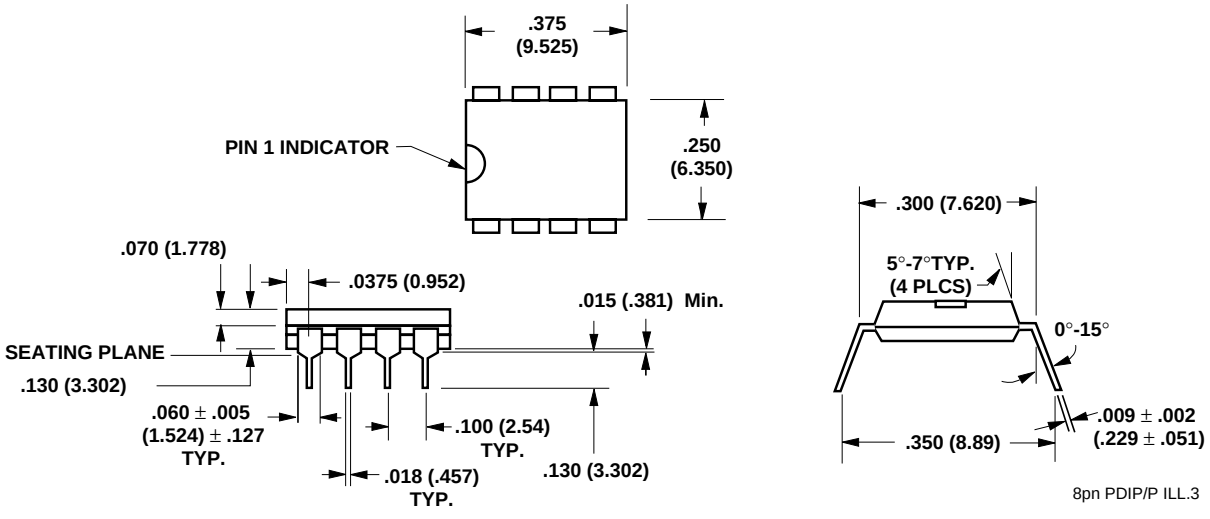
Figure 8. V_{LOCK} Timing Diagram

8 Pin SOIC (Type S) Package JEDEC (150 mil body width)



8pn JEDEC SOIC ILL.2

8 Pin PDIP (Type P) Package



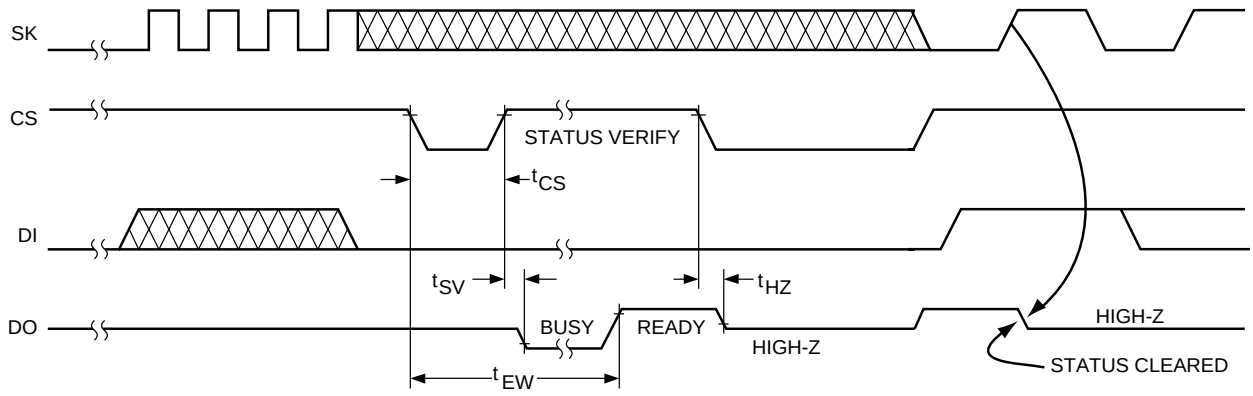
8pn PDIP/P ILL.3

Ready/Busy Status

During the internal write operation the S93VP462/VP463 memory array is inaccessible. After starting the write operation (taking CS low) the host can implement a 10ms timeout routine or alternatively it can employ a polling routine that tests the state of the DO pin.

After starting the write, testing for the status is easily accomplished by taking CS high and testing the state of DO. If it is low the device is still busy with the internal write. If it is high the write operation has completed.

For the polling routine the host has the option of toggling CS for each test of DO, or it can place CS high and then intermittently test DO. SK is not required for any of these operations. Once the device is ready, it will continue to drive DO high whenever the S93VP462/VP463 is selected. The ready state of DO can be cleared by clocking in a start bit; this start bit can either be the beginning of a new command sequence or it can be a dummy start bit with CS returning low before the host issues a new command.



2040 ILL13.0

ORDERING INFORMATION